



FP7G150US60

Transfer Molded Type IGBT Module

General Description

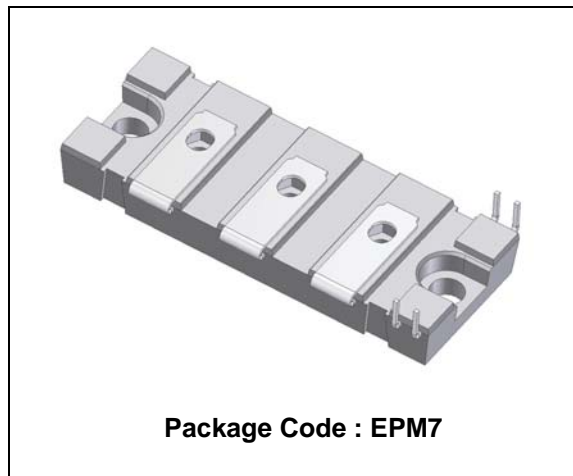
Fairchild's New IGBT Modules (Transfer Molded Type) provide low conduction and switching losses as well as short circuit ruggedness. They are designed for applications such as Motor control, Uninterrupted Power Supplies (UPS) and general Inverters where short circuit ruggedness is a required feature.

Features

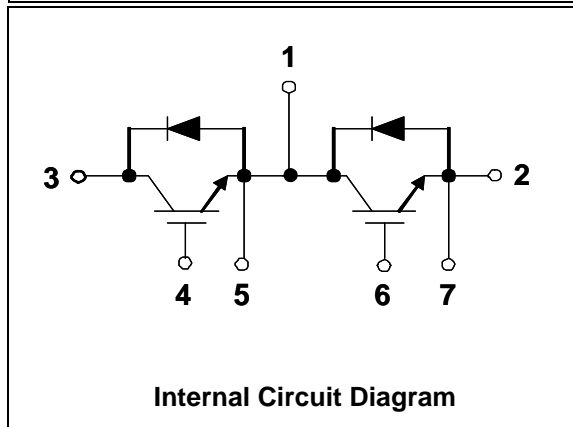
- Short Circuit rated 10us @Tc=100°C, Vge=15V
- High Speed Switching
- Low Saturation Voltage : Vce(sat) =2.3V @Ic=150A
- High Input Impedance
- Fast & Soft Anti-Parallel FWD

Application

- Welders
- AC & DC Motor Controls
- General Purpose Inverters
- Robotics
- Servo Controls
- UPS



Package Code : EPM7



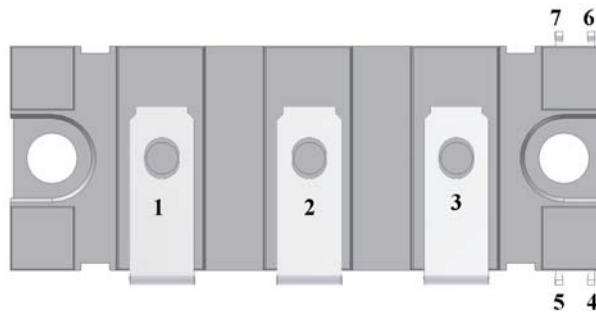
Internal Circuit Diagram

Absolute Maximum Ratings

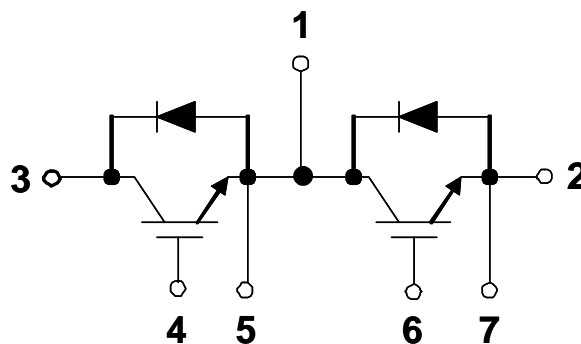
Symbol	Description	Rating	Units
V _{CES}	Collector-Emitter Voltage	600	V
V _{GES}	Gate-Emitter Voltage	± 20	V
I _C	Collector Current @ T _C = 25°C	150	A
I _{CM(1)}	Maximum Pulsed Collector Current	300	A
I _F	Diode Continuous Forward Current @ T _C = 100°C	150	A
I _{FM}	Diode Maximum Forward Current	300	A
T _{SC}	Short Circuit Withstand Time @ T _C = 100°C	10	us
P _D	Maximum Power Dissipation @ T _C = 25°C	450	W
T _J	Operating Junction Temperature	-40 to +125	°C
T _{stg}	Storage Temperature Range	-40 to +125	°C
V _{iso}	Isolation Voltage @ AC 1minute	2500	V
Mounting Torque	Power Terminals Screw : M5	2.0	N.m
	Mounting Screw : M5	2.0	N.m



Pin Configuration and Pin Description



Top View



Internal Circuit Diagram

Pin Description

Pin Number	Pin Description
1	Emitter of Q1, IGBT, Collector of Q2, IGBT
2	Emitter of Q2, IGBT
3	Collector of Q1, IGBT
4	Gate of Q1, IGBT
5	Emitter of Q1, IGBT
6	Gate of Q2, IGBT
7	Emitter of Q2, IGBT

Electrical Characteristics ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
--------	-----------	------------	-----	-----	-----	-------

Off Characteristics

BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	600	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coeff. of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	-	0.6	-	V
I_{CES}	Collector Cut-off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	-	-	250	μA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	-	-	± 100	nA

On Characteristics

$V_{GE(th)}$	G-E Threshold Voltage	$V_{GE} = 0V, I_C = 150mA$	5.0	6.0	8.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 150A, V_{GE} = 15V$	-	2.3	2.8	V

Dynamic Characteristics

C_{ies}	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ $f = 1MHz$		11.2		nF
C_{oes}	Output Capacitance			1.03		nF
C_{res}	Reverse Capacitance			0.1		nF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 150A,$ $R_G = 2.4\Omega, V_{GE} = 15V$ Inductive Load, $T_C = 25^\circ\text{C}$	-	45	-	ns
t_r	Rise Time		-	35	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	135	-	ns
t_f	Fall Time		-	70	-	ns
E_{on}	Turn-On Switching Loss		-	0.66	-	mJ
E_{off}	Turn-Off Switching Loss		-	2.7	-	mJ
E_{ts}	Total Switching Loss		-	3.36	-	mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 150A,$ $R_G = 2.4\Omega, V_{GE} = 15V$ Inductive Load, $T_C = 125^\circ\text{C}$	-	45	-	ns
t_r	Rise Time		-	35	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	160	-	ns
t_f	Fall Time		-	170	-	ns
E_{on}	Turn-On Switching Loss		-	1.5	-	mJ
E_{off}	Turn-Off Switching Loss		-	4.4	-	mJ
E_{ts}	Total Switching Loss		-	5.9	-	mJ
T_{sc}	Short Circuit Withstand Time	$V_{CC} = 300V, V_{GE} = 15V @ T_C = 100^\circ\text{C}$	10	-	-	μs
Q_g	Total Gate Charge	$V_{CE} = 300V, I_C = 150A, V_{GE} = 15V$	-	336	-	nC
Q_{ge}	Gate-Emitter Charge		-	68	-	nC
Q_{gc}	Gate-Collector Charge		-	178	-	nC

Electrical Characteristics of DIODE ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
V_{FM}	Diode Forward Voltage	$I_F = 150\text{A}$	$T_C = 25^\circ\text{C}$	-	1.8	2.8	V
			$T_C = 100^\circ\text{C}$	-	1.7	-	
t_{rr}	Diode Reverse Recovery Time	$I_F = 150\text{A}$ $di/dt = 300\text{ A/us}$	$T_C = 25^\circ\text{C}$	-	115	165	ns
			$T_C = 100^\circ\text{C}$	-	190	-	
I_{rr}	Diode Peak Reverse Recovery Current		$T_C = 25^\circ\text{C}$	-	23	33	A
			$T_C = 100^\circ\text{C}$	-	45	-	
Q_{rr}	Diode Reverse Recovery Charge		$T_C = 25^\circ\text{C}$	-	1322	-	nC
			$T_C = 100^\circ\text{C}$	-	4307	-	

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case (IGBT Part, per 1/2 Module)	-	0.22	$^\circ\text{C/W}$
$R_{\theta JC}$	Junction-to-Case (DIODE Part, per 1/2 Module)	-	0.54	$^\circ\text{C/W}$
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.05	-	$^\circ\text{C/W}$
Weight	Weight of Module	-	90	g

Typical Performance Characteristics

Fig 1. Typical Output Characteristics

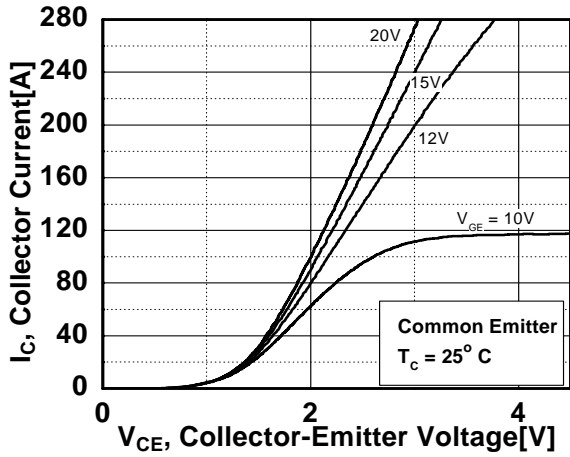


Fig 2. Typical Saturation Voltage Characteristics

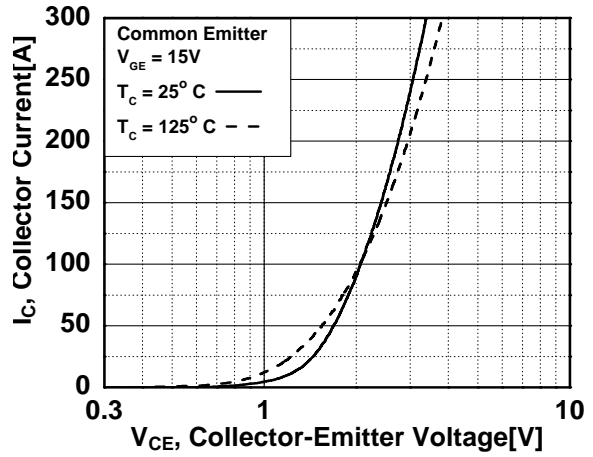


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

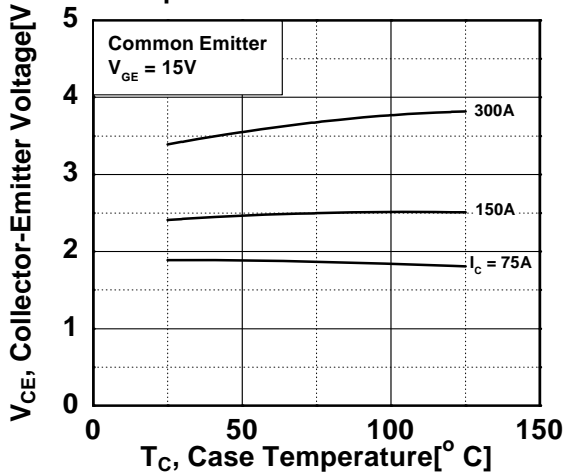


Fig 4. Load Current vs. Frequency

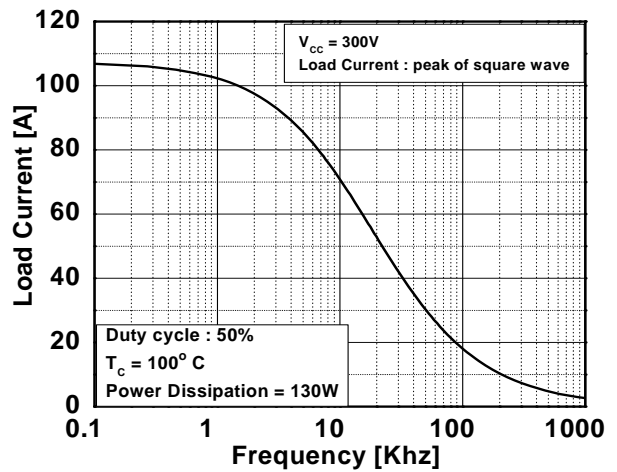


Fig 5. Saturation Voltage vs. V_{GE}

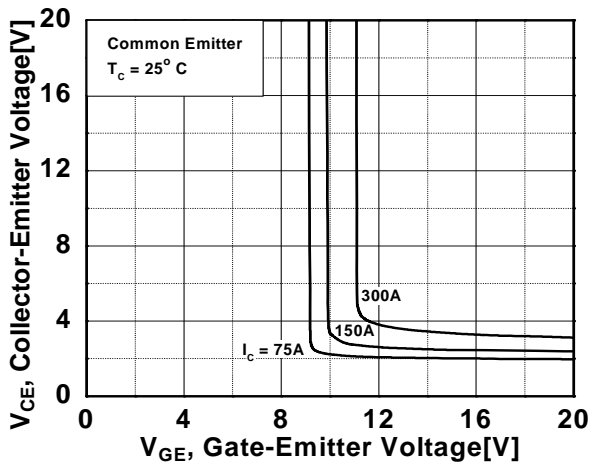


Fig 6. Saturation Voltage vs. V_{GE}

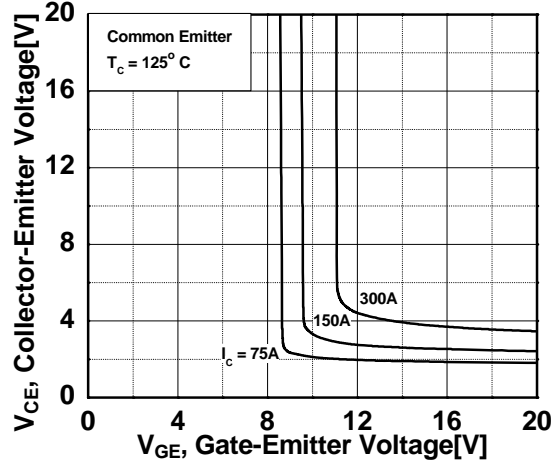


Fig 7. Capacitance Characteristic

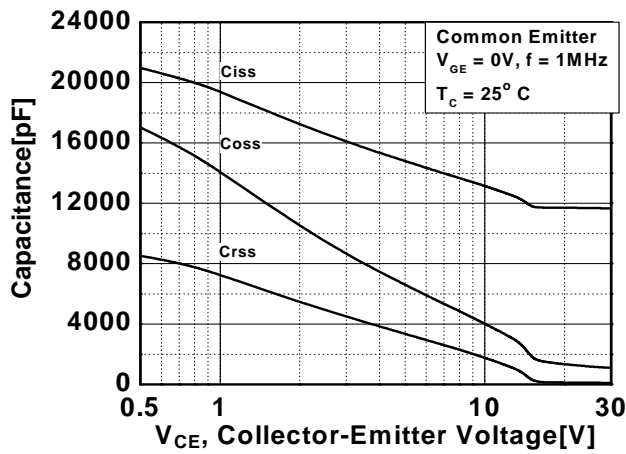


Fig 8. Turn-On Characteristics vs. Gate Resistance

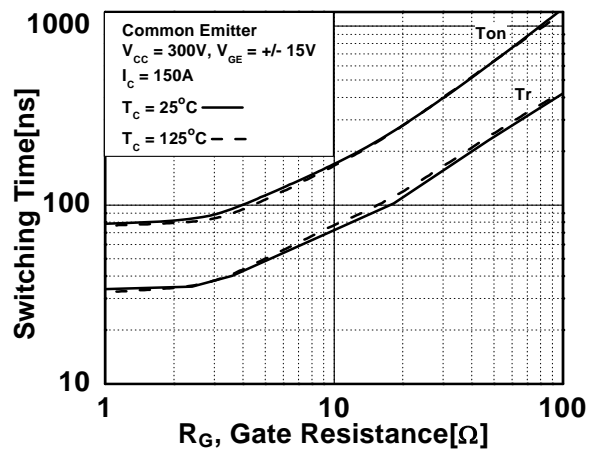


Fig 9. Turn-Off Characteristics vs. Gate Resistance

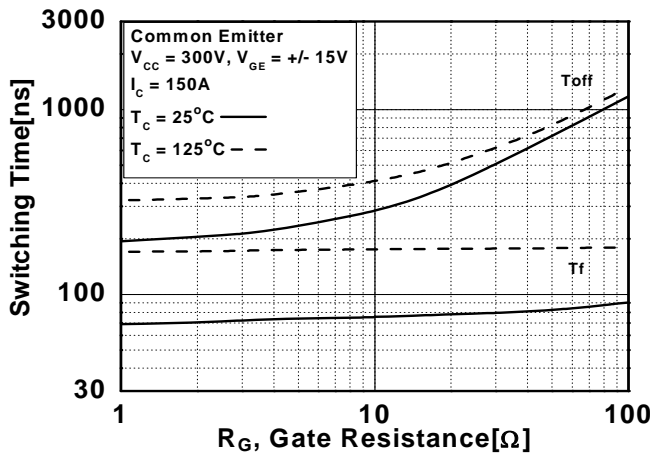


Fig 10. Switching Loss vs. Gate Resistance

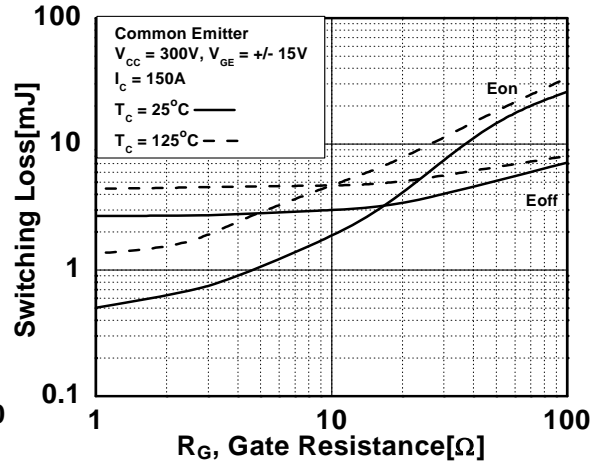


Fig 11. Turn-On Characteristics vs. Collector Current

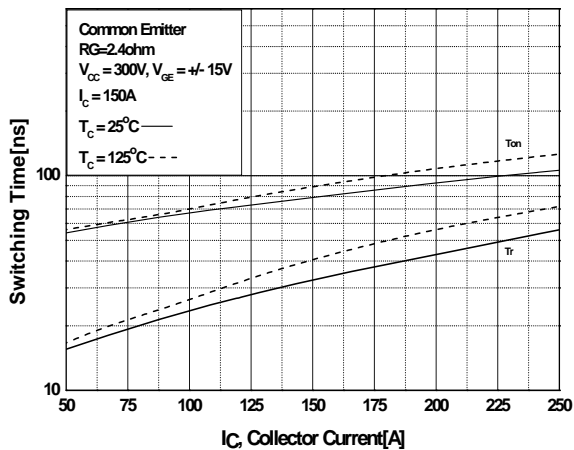


Fig 12. Turn-Off Characteristics vs. Collector Current

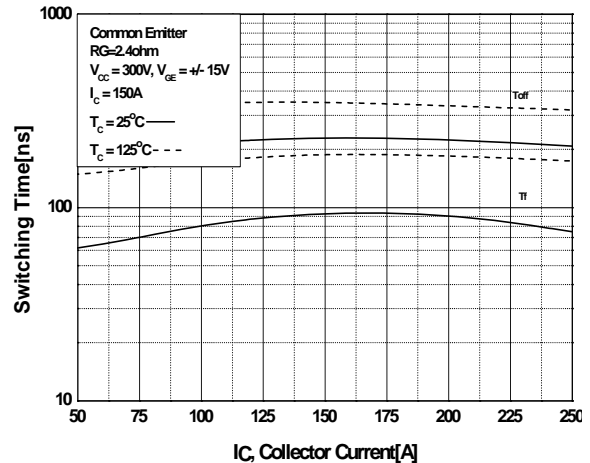


Fig 13. Switching Loss vs. Collector

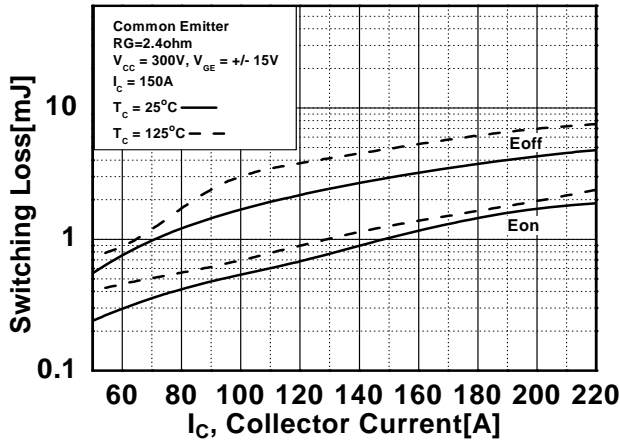


Fig 14. Gate Charge Characteristics

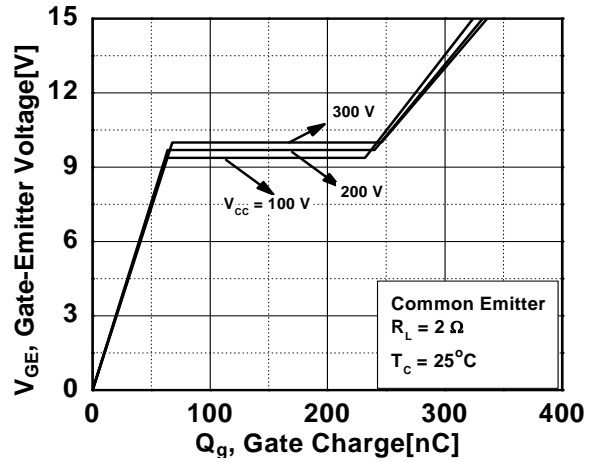


Fig 15. FBSOA Characteristics

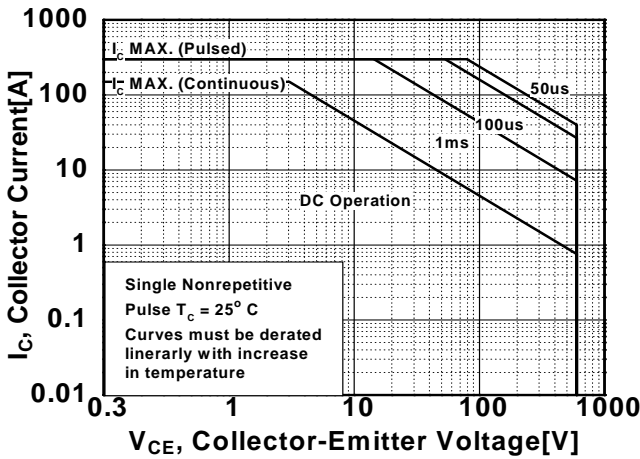


Fig 16. Turn-Off SOA Characteristics

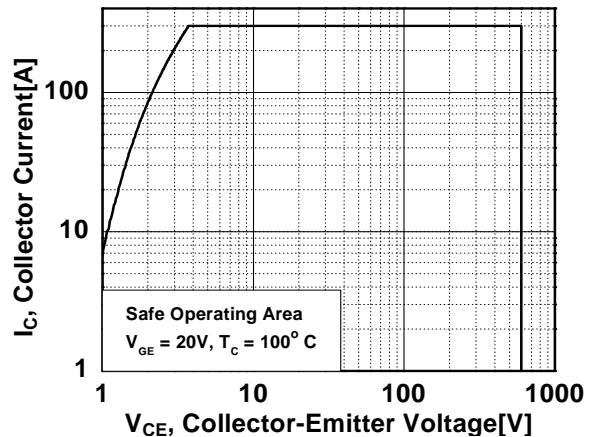


Fig 17. RBSOA Characteristics

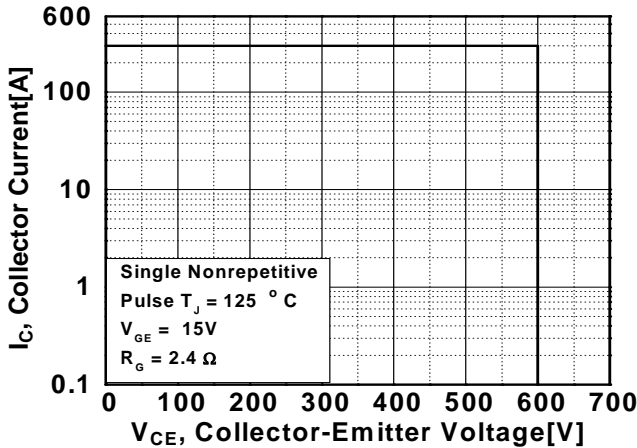


Fig 18. Transient Thermal Impedance

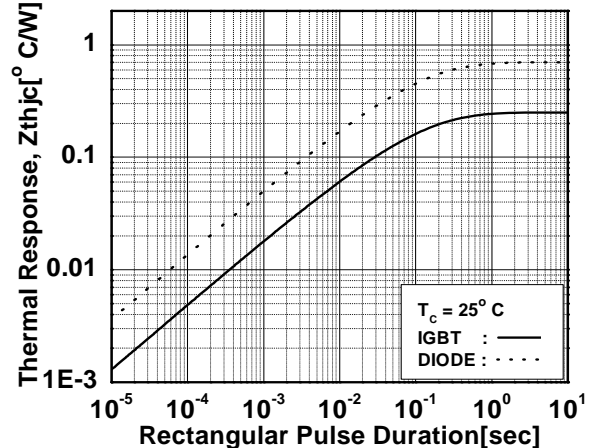


Fig 19. Forward Characteristics

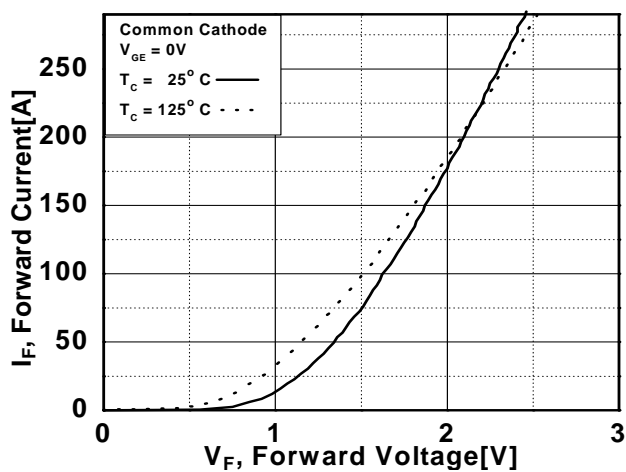
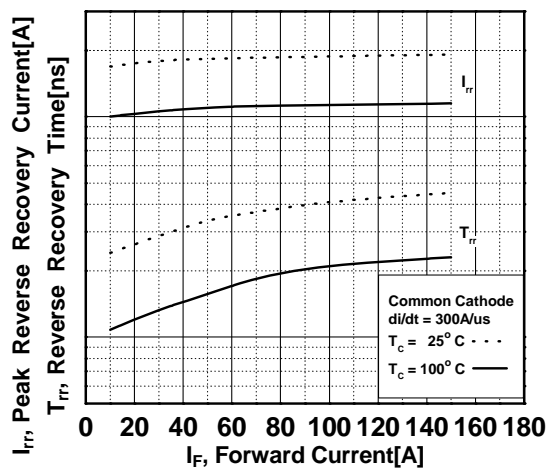
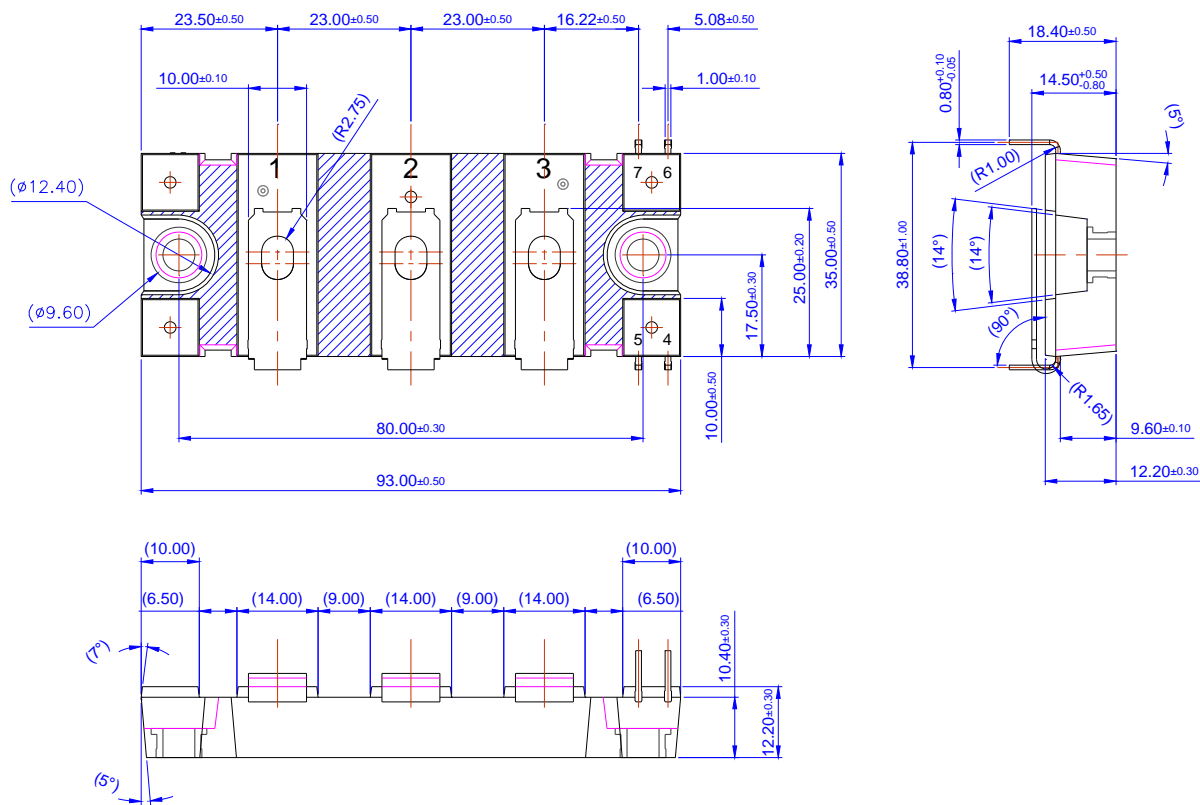


Fig 20. Reverse Recovery Characteristics



Detailed Package Outline Drawings



[查询"FP7G150US60"供应商](#)




FP7G150US60 Transfer Molded Type IGBT Module





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

- | | | | |
|--|---|--|---|
| ACEx [®] | FPS [™] | PDP-SPM [™] | The Power Franchise [®] |
| Build it Now [™] | F-PFS [™] | Power-SPM [™] | the power franchise |
| CorePLUS [™] | FRFET [®] | PowerTrench [®] | TinyBoost [™] |
| CorePOWER [™] | Global Power Resource SM | Programmable Active Droop [™] | TinyBuck [™] |
| CROSSVOLT [™] | Green FPS [™] | QFET [®] | TinyLogic [®] |
| CTL [™] | Green FPS [™] e-Series [™] | QS [™] | TINYOPTO [™] |
| Current Transfer Logic [™] | GTO [™] | Quiet Series [™] | TinyPower [™] |
| EcoSPARK [®] | IntelliMAX [™] | RapidConfigure [™] | TinyPWM [™] |
| EfficientMax [™] | ISOPLANAR [™] | Saving our world 1mW at a time [™] | TinyWire [™] |
| EZSWITCH [™] * | MegaBuck [™] | SmartMax [™] | μSerDes [™] |
|  [™] | MICROCOUPLER [™] | SMART START [™] |  |
|  [™] | MicroFET [™] | SPM [®] | UHC [®] |
| Fairchild [®] | MicroPak [™] | STEALTH [™] | Ultra FRFET [™] |
| Fairchild Semiconductor [®] | MillerDrive [™] | SuperFET [™] | UniFET [™] |
| FACT Quiet Series [™] | MotionMax [™] | SuperSOT [™] -3 | VCX [™] |
| FACT [®] | Motion-SPM [™] | SuperSOT [™] -6 | VisualMax [™] |
| FAST [®] | OPTOLOGIC [®] | SuperSOT [™] -8 | |
| FastvCore [™] | OPTOPLANAR [®] | SuperMOS [™] | |
| FlashWriter [®] * |  [®] |  | |

* EZSWITCH[™] and FlashWriter[®] are trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	This datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I34

